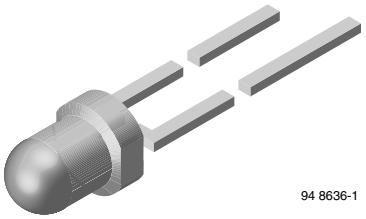
Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm): ∅ 3
- Peak wavelength: λ_p = 950 nm
- High reliability
- Angle of half intensity: φ = ± 16°
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector TEFT4300
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

Pb-free

e2

RoHS COMPLIANT

DESCRIPTION

TSUS4300 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue tinted plastic package.

APPLICATIONS

- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- Emitter in reflective sensors

PRODUCT SUMMARY				
COMPONENT	I_e (mW/sr)	φ (deg)	λ_P (nm)	t_r (ns)
TSUS4300	18	± 16	950	800

Note

Test conditions see table “Basic Characteristics”

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS4300	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.5, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	2	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	300	K/W

Note

T_{amb} = 25 °C, unless otherwise specified

For technical questions, contact: emittertechsupport@vishay.com
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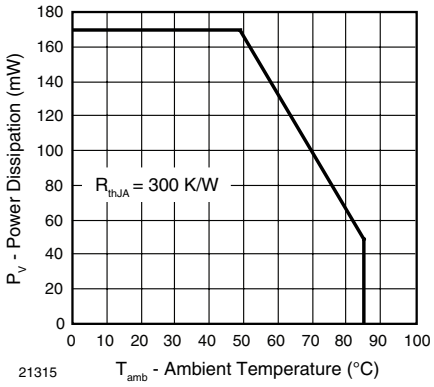


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

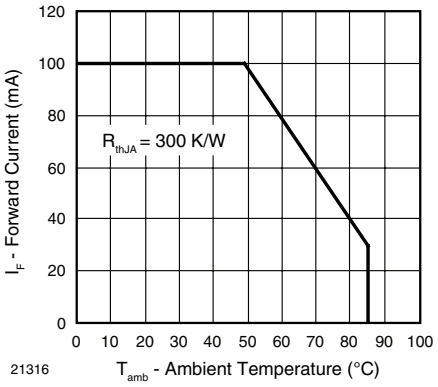


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.3	1.7	V
	I_F = 1.5 A, t_p = 100 µs	V_F		2.2		V
Temperature coefficient of V_F	I_F = 100 mA	TK_{VF}		- 1.3		mV/K
Reverse current	V_R = 5 V	I_R			100	µA
Breakdown voltage	I_R = 100 µA	$V_{(BR)}$	5	40		
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		30		pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	7	18	35	mW/sr
	I_F = 1.5 A, t_p = 100 µs	I_e		160		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e		20		mW
Temperature coefficient of ϕ_e	I_F = 20 mA	$TK\phi_e$		- 0.8		%/K
Angle of half intensity		φ		± 16		deg
Peak wavelength	I_F = 100 mA	λ_p		950		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.2		nm/K
Rise time	I_F = 100 mA	t_r		800		ns
	I_F = 1.5 A	t_r		400		ns
Fall time	I_F = 100 mA	t_f		800		ns
	I_F = 1.5 A	t_f		400		ns
Virtual source diameter		d		2.1		mm

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

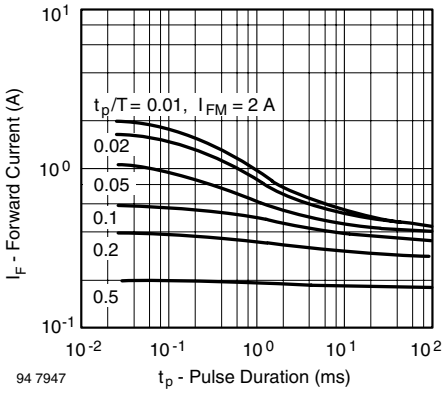


Fig. 3 - Pulse Forward Current vs. Pulse Duration

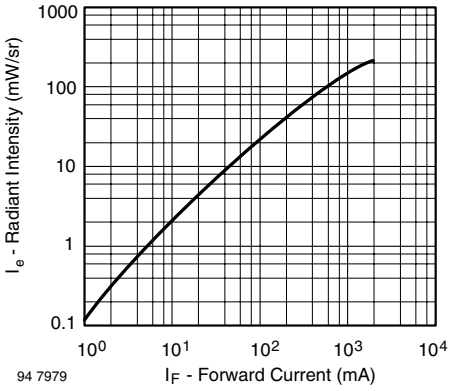


Fig. 6 - Radiant Intensity vs. Forward Current

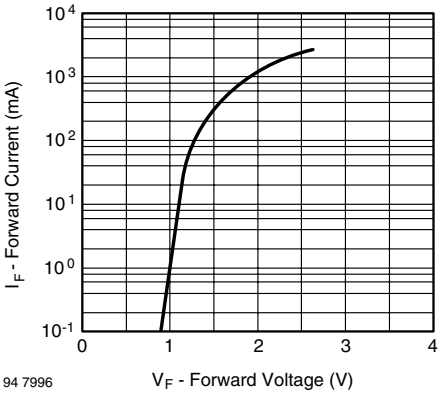


Fig. 4 - Forward Current vs. Forward Voltage

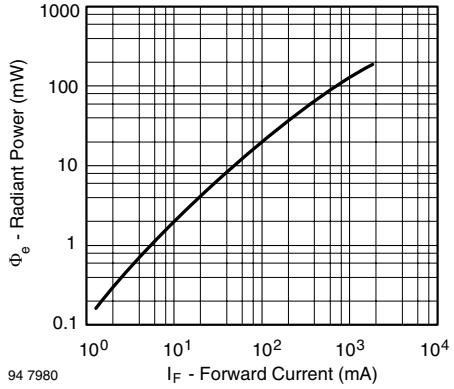


Fig. 7 - Radiant Power vs. Forward Current

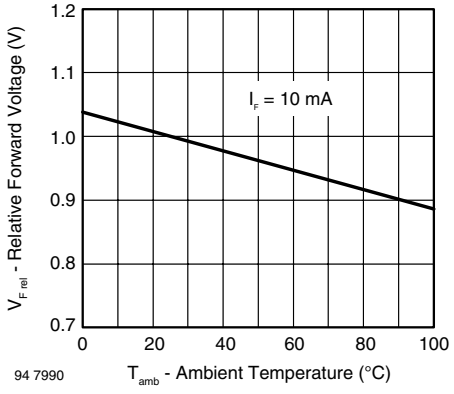


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

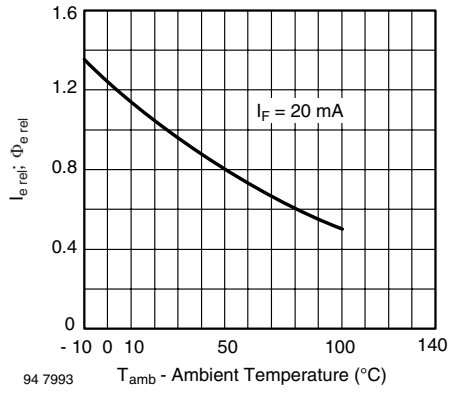


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

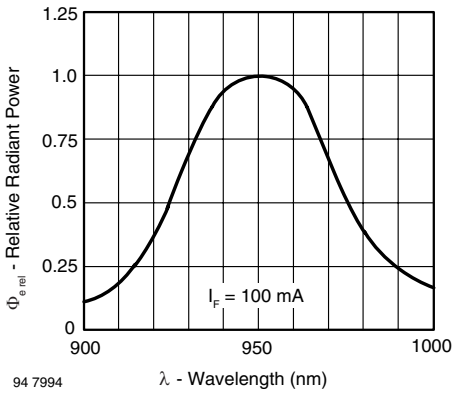


Fig. 9 - Relative Radiant Power vs. Wavelength

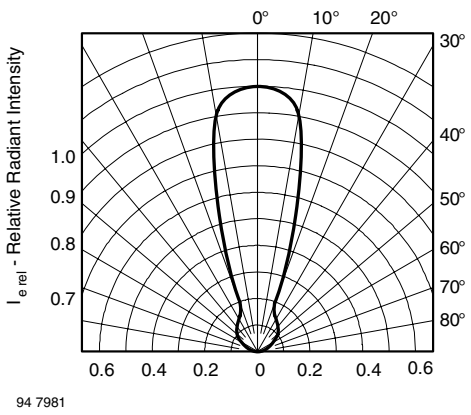
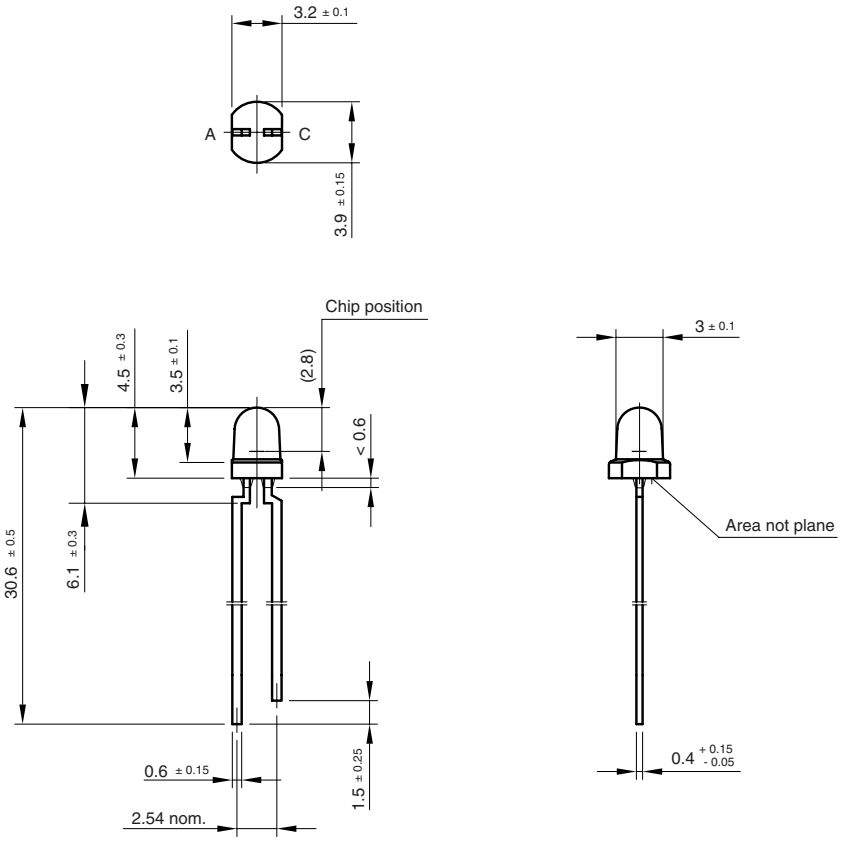


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5269.02-4
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